

# Cascadable Silicon Bipolar MMIC Amplifier

## Technical Data

#### **MSA-0386**

#### **Features**

- Cascadable 50  $\Omega$  Gain Block
- 3 dB Bandwidth: DC to 2.4 GHz
- 12.0 dB Typical Gain at 1.0 GHz
- 10.0 dBm Typical  $P_{1 dB}$  at 1.0 GHz
- Unconditionally Stable (k>1)
- Surface Mount Plastic Package
- Tape-and-Reel Packaging Option Available<sup>[1]</sup>

#### Note:

 Refer to PACKAGING section "Tapeand-Reel Packaging for Surface Mount Semiconductors".

## **Description**

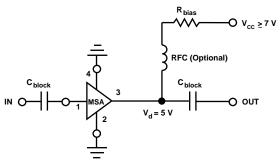
The MSA-0386 is a high performance silicon bipolar Monolithic Microwave Integrated Circuit (MMIC) housed in a low cost, surface mount plastic package. This MMIC is designed for use as a general purpose  $50~\Omega$  gain block. Typical applications include narrow and broad band IF and RF amplifiers in commercial and industrial applications.

The MSA-series is fabricated using HP's  $10\,\mathrm{GHz}\,\mathrm{f_T}, 25\,\mathrm{GHz}\,\mathrm{f_{MAX}},$  silicon bipolar MMIC process which uses nitride self-alignment, ion implantation, and gold metallization to achieve excellent performance, uniformity and reliability. The use of an external bias resistor for temperature and current stability also allows bias flexibility.

### 86 Plastic Package



## **Typical Biasing Configuration**



5965-9571E 6-314

## MSA-0386 Absolute Maximum Ratings

Parameter	Absolute Maximum <sup>[1]</sup>				
Device Current	70 mA				
Power Dissipation <sup>[2,3]</sup>	400 mW				
RF Input Power	+13dBm				
Junction Temperature	150℃				
Storage Temperature	-65 to 150°C				

Thermal Resistance $^{[2,4]}$ :	
$\theta_{\rm jc} = 115$ °C/W	

#### **Notes:**

- 1. Permanent damage may occur if any of these limits are exceeded.
- 2.  $T_{CASE} = 25$ °C.
- 3. Derate at 9.5 mW/°C for  $T_{\rm C} > 116$  °C.
- 4. See MEASUREMENTS section "Thermal Resistance" for more information.

# Electrical Specifications<sup>[1]</sup>, $T_A = 25$ °C

Symbol	Parameters and Test Conditions: I	Units	Min.	Тур.	Max.	
GP	Power Gain $( S_{21} ^2)$	f = 0.1 GHz			12.5	
		f = 1.0  GHz		10.0	12.0	
$\Delta G_{P}$	Gain Flatness	f = 0.1  to  1.6  GHz	dB		± 0.7	
f <sub>3 dB</sub>	3 dB Bandwidth		GHz		2.4	
VSWR	Input VSWR	f = 0.1  to  3.0  GHz			1.5:1	
VSWK	Output VSWR	f = 0.1  to  3.0  GHz			1.7:1	
NF	$50\Omega$ Noise Figure	f = 1.0  GHz	dB		6.0	
P <sub>1 dB</sub>	Output Power at 1 dB Gain Compression	f = 1.0  GHz	dBm		10.0	
IP <sub>3</sub>	Third Order Intercept Point	f = 1.0  GHz	dBm		23.0	
$t_{\mathrm{D}}$	Group Delay	f = 1.0  GHz	psec		140	
Vd	Device Voltage		V	4.0	5.0	6.0
dV/dT	Device Voltage Temperature Coefficient		mV/°C		-8.0	

#### Note

## **Part Number Ordering Information**

Part Number	No. of Devices	Container					
MSA-0386-TR1	1000	7" Reel					
MSA-0386-BLK	100	Antistatic Bag					

For more information, see "Tape and Reel Packaging for Semiconductor Devices".

<sup>1.</sup> The recommended operating current range for this device is 20 to 40 mA. Typical performance as a function of current is on the following page.

MSA-0386 Typical Scattering Parameters (Z  $_{0}$  = 50  $\Omega,$   $T_{_{A}}$  = 25  $^{\circ}C,$   $I_{_{d}}$  = 35 mA)

Freq.	S <sub>11</sub>		$\mathbf{S}_{21}$		$S_{12}$			$\mathbf{S}_{22}$		
GHz	Mag	Ang	dB	Mag	Ang	dB	Mag	Ang	Mag	Ang
0.1	.11	174	12.5	4.22	175	-18.3	.122	1	.13	-11
0.2	.11	169	12.5	4.20	170	-18.2	.124	2	.13	-20
0.4	.11	159	12.4	4.16	159	-18.1	.124	5	.14	<b>-4</b> 1
0.6	.10	149	12.2	4.09	149	-17.9	.128	8	.15	-60
0.8	.10	142	12.1	4.00	139	-17.6	.131	9	.16	-78
1.0	.09	137	11.9	3.93	129	-17.4	.136	11	.18	<b>-</b> 93
1.5	.09	139	11.2	3.61	106	-16.6	.149	14	.20	-129
2.0	.12	149	10.3	3.28	83	-15.3	.171	13	.23	-157
2.5	.18	150	9.4	2.95	66	-14.4	.190	12	.26	-176
3.0	.25	142	8.3	2.60	48	-13.7	.207	9	.29	167
3.5	.32	133	7.2	2.29	31	-13.2	.219	3	.30	152
4.0	.40	124	6.0	2.01	15	-13.0	.224	-1	.31	142
5.0	.53	106	3.7	1.53	<b>-</b> 13	-12.8	.228	-11	.32	128

A model for this device is available in the DEVICE MODELS section.

# Typical Performance, $T_A = 25^{\circ}C$

(unless otherwise noted)

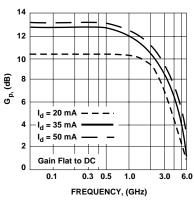


Figure 1. Typical Power Gain vs. Frequency,  $T_A = 25^{\circ}C$ .

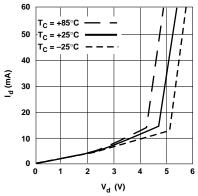


Figure 2. Device Current vs. Voltage.

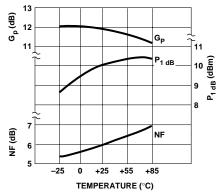


Figure 3. Output Power at 1 dB Gain Compression, NF and Power Gain vs. Case Temperature,  $f=1.0~\mathrm{GHz},$   $I_d=35\mathrm{mA}.$ 

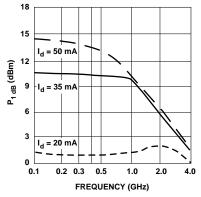


Figure 4. Output Power at 1 dB Gain Compression vs. Frequency.

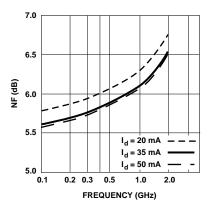
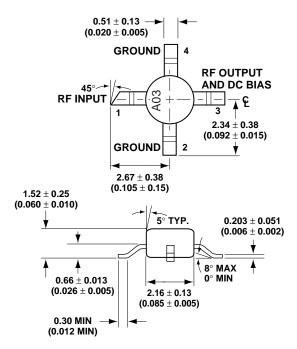


Figure 5. Noise Figure vs. Frequency.

## **86 Plastic Package Dimensions**



**DIMENSIONS ARE IN MILLIMETERS (INCHES)**